

# TRANSISTOR MODULE (THREE PHASES BRIDGE TYPE)

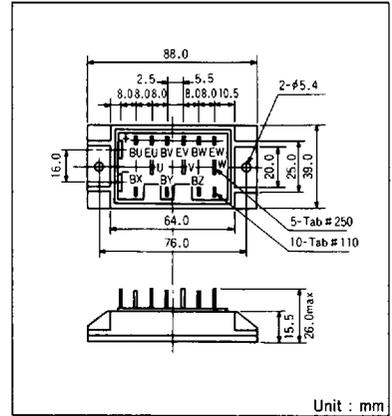
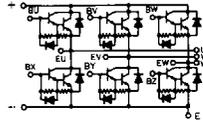
## QF20AA40/60

QF20AA is a six pack Darlingtion power transistor module which has six transistors connected in three phase bridge configuration. Each transistor has a reverse paralleled fast recovery diode. The mounting base of the module is electrically isolated from semiconductor elements for simple heatsink construction.

- $I_C = 20A$   $V_{CEX} = 400/600V$
- Low saturation voltage for higher efficiency.
- High DC current gain  $h_{FE}$
- Isolated mounting base
- $V_{EBO} 10V$  for faster switching speed.

(Applications)

Motor Control (VVVF), AC Servo, UPS



Unit : mm  
T<sub>j</sub> = 25°C

### Maximum Ratings

Symbol	Item	Conditions	Ratings		Unit
			QF20AA40	QF20AA60	
V <sub>CBO</sub>	Collector-Base Voltage		400	600	V
V <sub>CEX</sub>	Collector-Emitter Voltage	V <sub>BE</sub> = -2V	400	600	V
V <sub>EBO</sub>	Emitter-Base Voltage		10		V
I <sub>C</sub>	Collector Current	( ) = pw ≤ 1ms	20 (40)		A
-I <sub>C</sub>	Reverse Collector Current		20		A
I <sub>B</sub>	Base Current		2		A
P <sub>T</sub>	Total power dissipation	T <sub>c</sub> = 25°C	160		W
T <sub>j</sub>	Junction Temperature		-40 ~ +150		°C
T <sub>stg</sub>	Storage Temperature		-40 ~ +125		°C
V <sub>ISO</sub>	Isolation Voltage	A.C. 1minute	2500		V
	Mounting Torque(M5)	Recommended Value 1.5~2.5 (15~25)	2.7 (28)		N·m (kgf·cm)
	Mass	Typical value	95		g

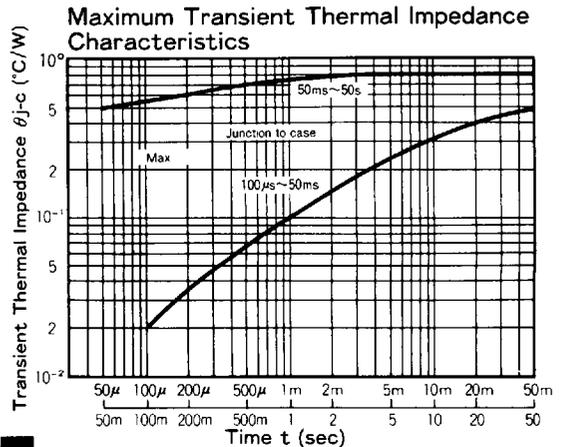
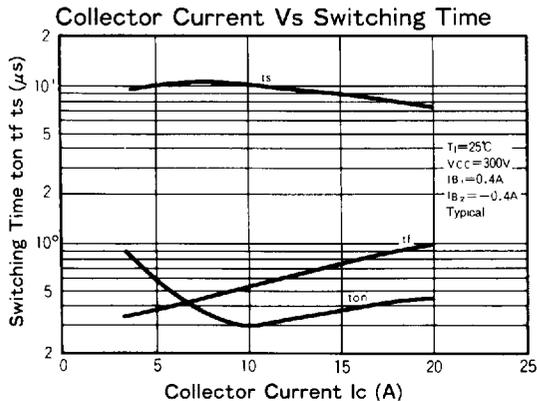
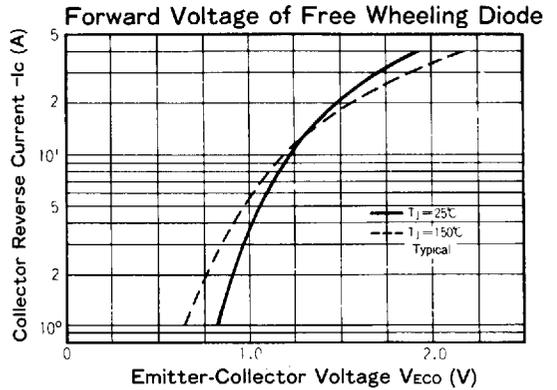
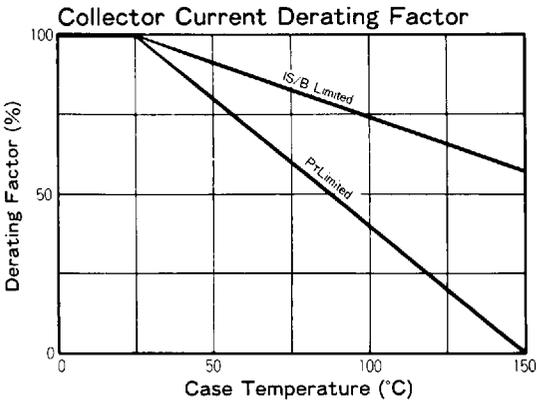
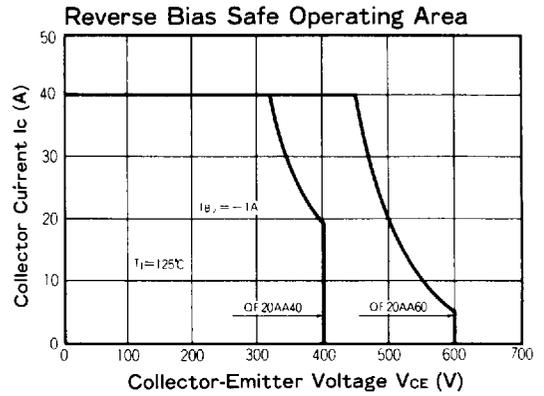
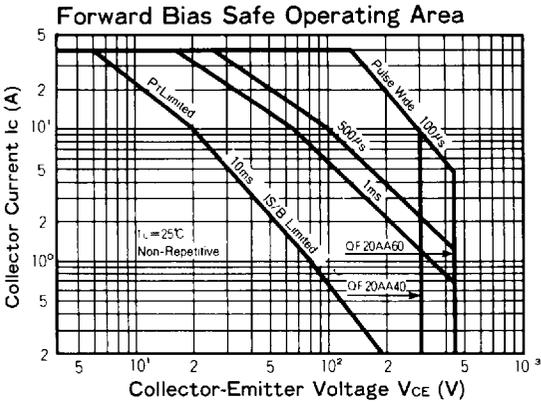
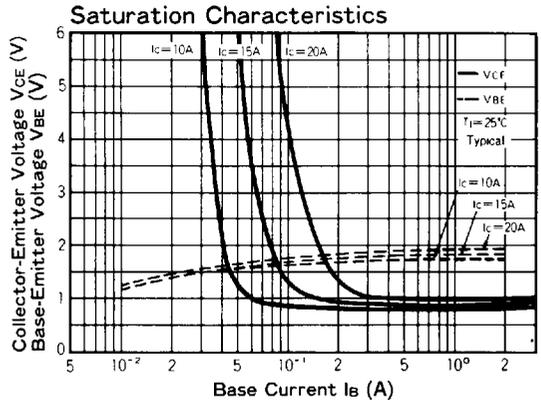
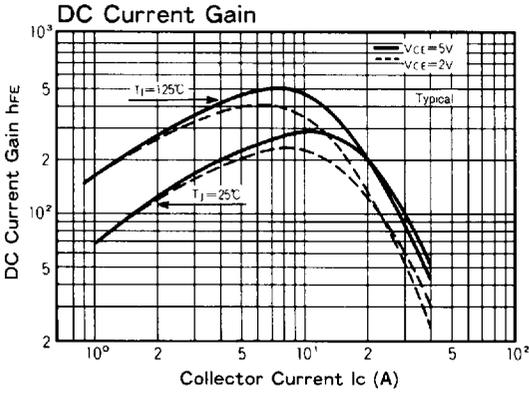
### Electrical Characteristics

T<sub>j</sub> = 25°C

Symbol	Item	Conditions	Ratings		Unit
			Min.	Max.	
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = V <sub>CBO</sub>		1.0	mA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = V <sub>EBO</sub>		200	mA
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	QF20AA40	I <sub>C</sub> = 1A	300	V
		QF20AA60		450	
V <sub>CEX(SUS)</sub>	Sustaining Voltage	QF20AA40	I <sub>C</sub> = 4A I <sub>B2</sub> = -1A	400	V
		QF20AA60		600	
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 20A V <sub>CE</sub> = 2V		75	
		I <sub>C</sub> = 20A V <sub>CE</sub> = 5V		100	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 20A I <sub>B</sub> = 0.27A		2.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 20A I <sub>B</sub> = 0.27A		2.5	V
ton	Switching Time	On Time	V <sub>CC</sub> = 300V I <sub>C</sub> = 20A I <sub>B1</sub> = 0.5A I <sub>B2</sub> = -0.5A	1.0	μs
ts		Storage Time		12.0	
tf		Fall Tjme		2.0	
V <sub>ECO</sub>	Collector-Emitter Reverse Voltage	-I <sub>C</sub> = 20A		1.6	V
R <sub>th(j-c)</sub>	Thermal Impedance (junction to case)	Transistor part		0.8	°C/W
		Diode part		2.2	

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